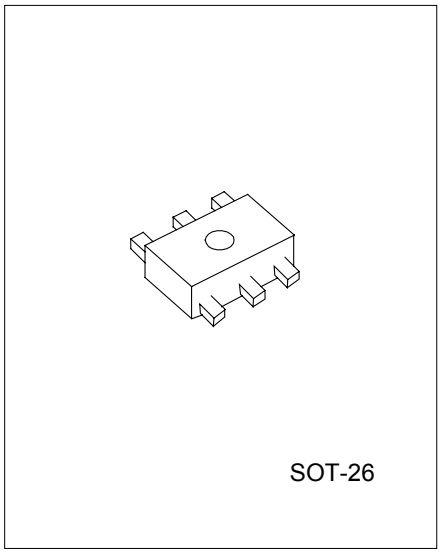
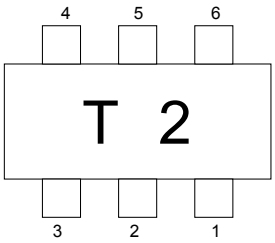
GENERAL PURPOSE DUAL TRANSISTOR



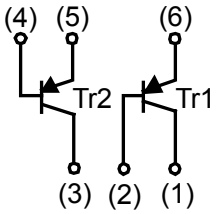
FEATURES

*Two 2SA1037 chips in a SMT package

MARKING



EQUIVALENT CIRCUITS



PIN 1 : Collector (1) PIN 4 : Base (2)

PIN 2 : Base (1) PIN 5 : Emitter (2)

PIN 3 : Collector (2) PIN 6 : Emitter (1)

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	Ic	150	mA
Collector Power Dissipation (total)	Pc	300 (note)	mW
Junction Temperature	Tj	150	°C
Storage Temperature	TSTG	-55~+150	°C

Note: 200mW per element must not be exceeded.

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	I_C= -50μA	-60			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C= -1mA	-50			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=-50μA	-6			V
Collector Cut-Off Current	I_{CBO}	V_{CB}= -60V			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}= -6V			-0.1	μA
Collector-Emitter Saturation Voltage	V_{CE}(sat)	I_C / I_B = -50mA/-5mA			-0.5	V
DC Current Transfer Ratio	h_{FE}	V_{CE}= -6V,I_C= -1mA	120		560	
Transition Frequency	f_T	V_{CE}=-12V,I_E=2mA,f=100MHz (note)		140		MHz
Output Capacitance	Cob	V_{CB}= -12V,I_E=0mA,f=1MHz		4	5	pF

Note: Transition frequency of the device.

CLASSIFICATION OF hFE

RANK	Q	R	S
RANGE	120-270	180-390	270-560